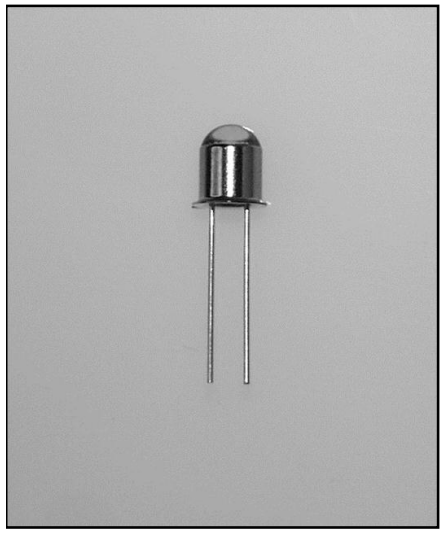
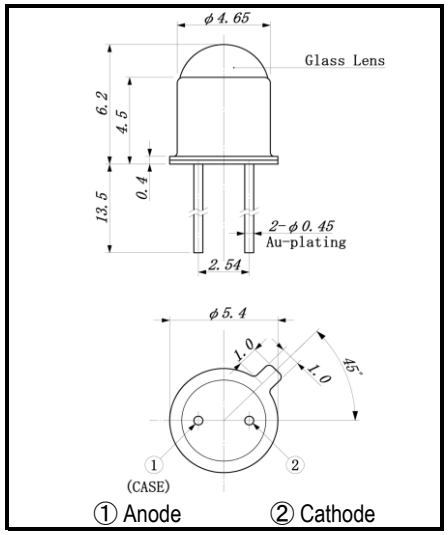
LS860N

Infrared Emitting Diode





Dimensions (Unit:mm)

FEATURES
- High-output Power
- Narrow Beam Angle
- High Reliability

APPLICATIONS
- Optical Switches
- Optical Emitters

1. ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

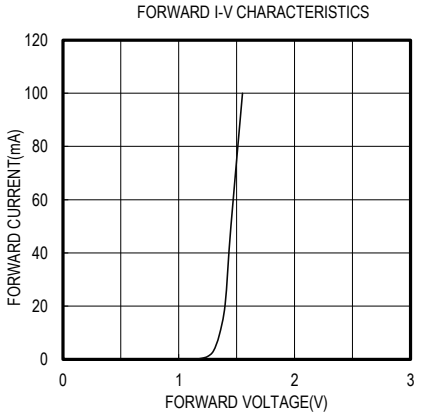
I T E M	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	100	mA
Forward Current (Pulse)*1	IFP	1	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	190	mW
Operating Temp.	Topr	-20 TO 85	℃
Storage Temp.	Tstg	-30 TO 100	℃
Junction Temp.	Tj	100	℃
Lead Soldering Temp.*2	Tls	260	℃

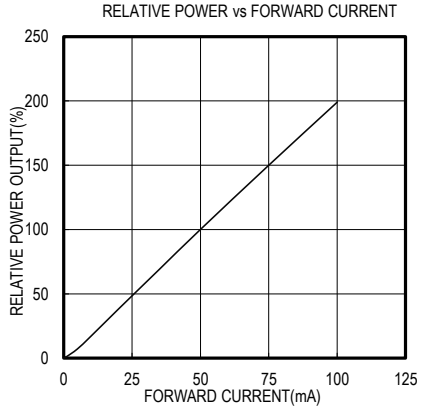
*1:Tw=10uS,T=1mS

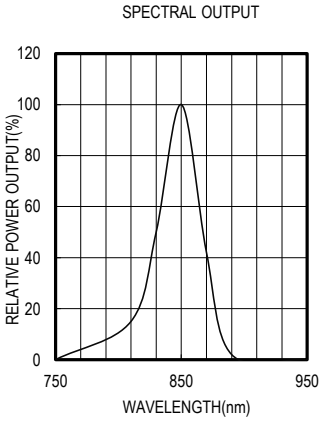
*2:Time 5 Sec max,Position:Up to 3mm from the body

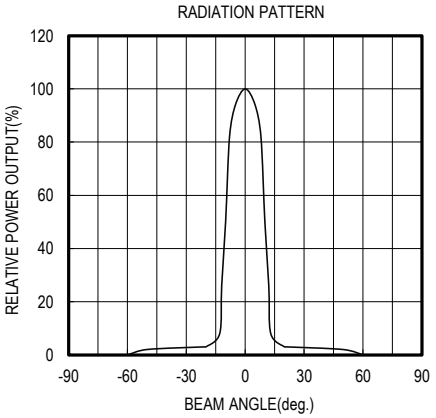
2.ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25℃)

I T E M	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=50mA		18.0		mW
Forward Voltage	VF	IF=50mA		1.45	1.9	V
Reverse Current	IR	VR=5V			10	μA
Peak Wavelength	λp	IF=50mA		850		nm
Spectral Line Half Width	Δλ	IF=50mA		30		nm
Half Intensity Beam Angle	θ	IF=50mA		±10		deg.









OPTRANS

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